

General Description

The SN74AUP1G126 is a single non-inverting buffer with 3-State output from ultra low power series, which can operate from a 0.8V to 3.6V supply. This device is fabricated with advanced CMOS technology to achieve ultra-high speed with high output drive.

Features

- Designed for 0.8V to 3.6V VCC Operation
- Low static power consumption; $ICC = 0.7\mu A$ (maximum)
- 4mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current Substantially Reduces System Power Requirements
- These Devices are Pb-Free and are RoHS Compliant

Pin Configuration

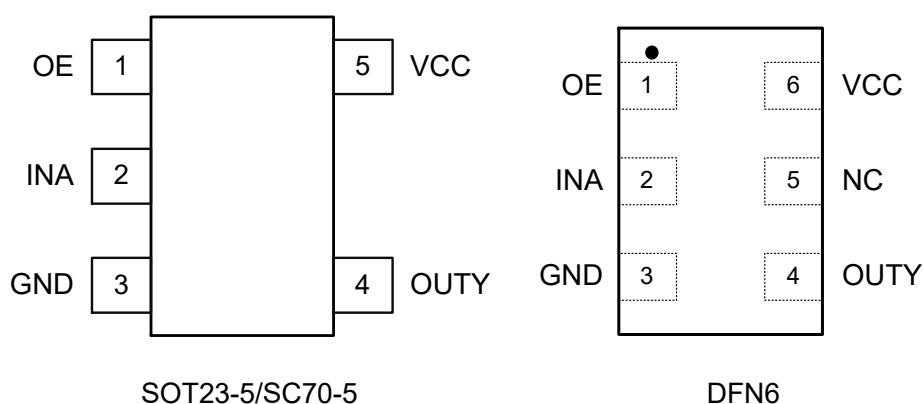


Figure1. Top View

Pin Function

SC70-5/ SOT23-5

Pin No.	Function
1	OE
2	INA
3	GND
4	OUTY
5	VCC

DFN6

Pin No.	Function
1	OE
2	INA
3	GND
4	OUTY
5	NC
6	VCC

Block Diagram

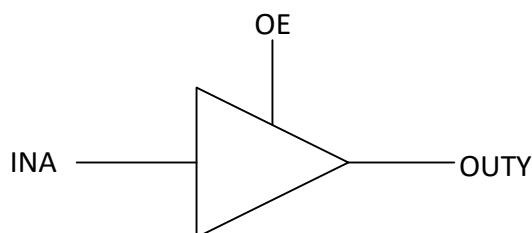


Figure2.

Functional Description

Function Table

Input		Output
OE	INA	OUTY
H	L	L
H	H	H
L	X	Z

Absolute Maximum Ratings

Symbol	Parameter		Value	Unit
V_{CC}	DC Supply Voltage		-0.5 to 4.6	V
V_I	DC Input Voltage		$-0.5 \leq V_I \leq +4.6$	V
V_O	DC Output Voltage Output in Higher or Low State ⁽¹⁾		-0.5 to 4.6	V
I_{IK}	DC Input Diode Current	$V_I < GND$	-50	mA
I_{OK}	DC Output Diode Current	$V_O < GND, V_O > V_{CC}$	± 50	mA
I_O	DC Output Sink Current		± 20	mA
I_{CC}	DC Supply Current per Supply Pin		± 50	mA
I_{GND}	DC Ground Current per Supply Pin		± 50	mA
T_{STG}	Storage Temperature Range		-65 to 150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
T_J	Junction Temperature Under Bias		150	°C
P_D	Power Dissipation in Still Air at 85°C		200	mW
ESD	ESD Classification	Human Body Model ⁽²⁾	4000	V
		Machine Model ⁽³⁾	200	
		Charged Device Model ⁽⁴⁾	1000	
I_{LU}	Latchup Current Above V_{CC} and GND at 125°C ⁽⁵⁾		± 100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Notes:

1. IO absolute maximum rating must be observed.
2. Tested to EIA/JESD22-A114-A, rated to EIA/JESD22-A114-B.
3. Tested to EIA/JESD22-A115-A, rated to EIA/JESD22-A115-A.
4. Tested to JESD22-C101-A.
5. Tested to EIA/JESD78.

Recommended Operating Conditions

Symbol	Parameter		Min	Max	Unit
V_{CC}	DC Supply Voltage Operating		0.8	3.6	V
V_{IN}	DC Input Voltage		0	3.6	V
V_{OUT}	DC Output Voltage (High or Low State)		0	3.6	V
T_A	Operating Temperature Range		-40	85	°C
t_r, t_f	Input Rise and Fall Time	$V_{CC} = 0.8V \text{ to } 3.6V$	0	20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied.

Electrical Characteristics

DC Electrical Characteristics

Symbol	Parameter	Condition	V _{cc} (V)	T _A = 25°C			-40°C ≤ T _A ≤ 85°C		Unit
				Min	Typ	Max	Min	Max	
V _{IH}	High-Level Input Voltage		0.8V	0.75V _{cc}			0.75V _{cc}		V
			0.9 to 1.95V	0.7V _{cc}			0.7V _{cc}		
			2.3 to 2.7V	1.6			1.6		
			3.0 to 3.6V	2.0			2.0		
V _{IL}	Low-Level Input Voltage		0.8V			0.25V _{cc}		0.25V _{cc}	V
			0.9 to 1.95V			0.3V _{cc}		0.3V _{cc}	
			2.3 to 2.7V			0.7		0.7	
			3.0 to 3.6V			0.9		0.9	
V _{OH}	High-Level Output Voltage	I _{OH} =-20µA	0.8 to 3.6V	V _{cc} -0.1			V _{cc} -0.1		V
		I _{OH} =-1.1mA	1.1	0.82	1.02		0.77		
		I _{OH} =-1.7mA	1.4	1.11	1.32		1.03		
		I _{OH} =-1.9mA	1.65	1.32	1.58		1.30		
		I _{OH} =-2.3mA	2.3	2.05	2.24		1.97		
		I _{OH} =-3.1mA		1.9	2.22		1.85		
		I _{OH} =-2.7mA	3.0	2.72	2.95		2.67		
		I _{OH} =-4.0mA		2.6	2.92		2.55		
V _{OL}	Low-Level Output Voltage	I _{OL} =20µA	0.8 to 3.6V			0.1		0.1	V
		I _{OL} =1.1mA	1.1		0.11	0.33		0.33	
		I _{OL} =1.7mA	1.4		0.12	0.31		0.37	
		I _{OL} =1.9mA	1.65		0.11	0.31		0.35	
		I _{OL} =2.3mA	2.3		0.14	0.31		0.33	
		I _{OL} =3.1mA			0.19	0.44		0.45	
		I _{OL} =2.7mA	3.0		0.11	0.31		0.33	
		I _{OL} =4.0mA			0.16	0.44		0.45	
I _{IN}	Input Leakage Current	V _{IN} = V _{CC} or GND	0 to 3.6V			±0.1		±0.2	uA
I _{OFF}	Power Off Leakage Current	V _{IN} = 3.6 V or V _{OUT} = 3.6 V	0			±0.2		±0.5	uA
I _{CC}	Quiescent Supply Current	V _{IN} = 3.6V or GND	3.6			±0.2		±0.7	uA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC Electrical Characteristics $t_r = t_f = 2.5\text{ns}$

Symbol	Parameter	Condition	$V_{CC}(\text{V})$	$T_A = 25^\circ\text{C}$			$-40^\circ\text{C} \leq T_A \leq 85^\circ\text{C}$		Unit
				Min	Typ	Max	Min	Max	
t_{PLH} t_{PHL}	Propagation Delay (Figure 3 And 4)	$C_L = 5 \text{ pF}^{(6)}$	0.8	13.2	29	90.1	11.9	220	ns
			1.2	5.0	7.6	14.3	4.6	14.4	
			1.5	3.4	4.8	8.9	3	9.6	
			1.8	2.7	3.6	6.9	2.3	7.6	
			2.5	1.9	2.4	5.1	1.6	5.6	
			3.3	1.5	1.9	4.4	1.3	4.8	
		$C_L = 10 \text{ pF}^{(6)}$	0.8	14.3	31.3	97.9	12.8	239	ns
			1.2	5.4	8.3	15.3	5.0	15.3	
			1.5	3.7	5.2	9.5	3.2	10.2	
			1.8	2.9	3.9	7.4	2.5	8.1	
			2.5	2.0	2.6	5.4	1.7	6.0	
			3.3	1.6	2.0	4.6	1.3	5.1	
		$C_L = 15 \text{ pF}^{(6)}$	0.8	15.3	32.5	106	13.8	259	ns
			1.2	5.8	8.9	16.3	5.3	16.3	
			1.5	4.0	5.6	10.1	3.5	10.9	
			1.8	3.1	4.2	7.8	2.6	8.6	
			2.5	2.1	2.8	5.8	1.8	6.4	
			3.3	1.7	2.2	4.9	1.4	5.4	
		$C_L = 30 \text{ pF}^{(6)}$	0.8	18.3	37.5	130	16.6	323	ns
			1.2	7.0	10.7	19.3	6.4	19.3	
			1.5	4.8	6.9	12.0	4.2	12.9	
			1.8	3.7	5.1	9.2	3.2	10.2	
			2.5	2.6	3.5	6.7	2.2	7.5	
			3.3	2.0	2.2	5.6	1.7	6.3	

Note6. C_L includes probe and jig capacitance.

Capacitance Characteristics

Symbol	Parameter	Condition	Typical	Unit
C_{IN}	Input Capacitance	$V_{CC} = 3.6V, V_I = 0 V$ or V_{CC}	2	pF
C_O	output capacitance	$V_{CC} = 0V, V_{OUT} = GND$	3	pF
C_{PD}	Power Dissipation Capacitance ⁽⁷⁾	1 MHz, $V_I = 0 V$ to V_{CC}	$V_{CC} = 0.8V$	7.6
			$V_{CC} = 1.2V$	8.1
			$V_{CC} = 1.5V$	8.5
			$V_{CC} = 1.8V$	8.6
			$V_{CC} = 2.5V$	9.0
			$V_{CC} = 3.3 V$	9.6

Note7. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:

$I_{CC(OPR)} = C_{PD} \times V_{CC} \times f_{in} + I_{CC} \times C_{PD}$ is used to determine the no-load dynamic power consumption;
 $P_D = C_{PD} \times V_{CC}^2 \times f_{in} + I_{CC} \times V_{CC} \times f_{in}$.

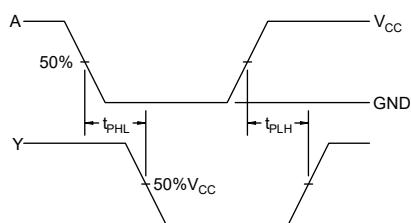


Figure 3. Switching Waveforms

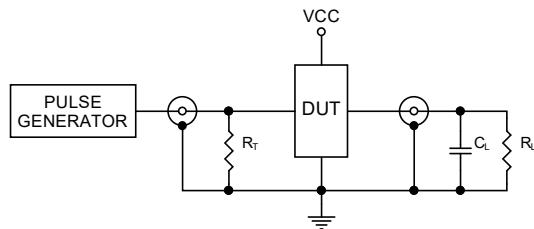
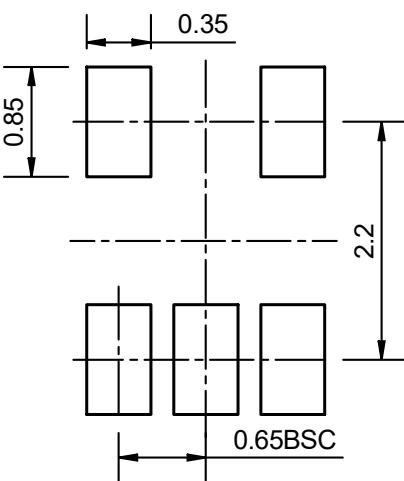
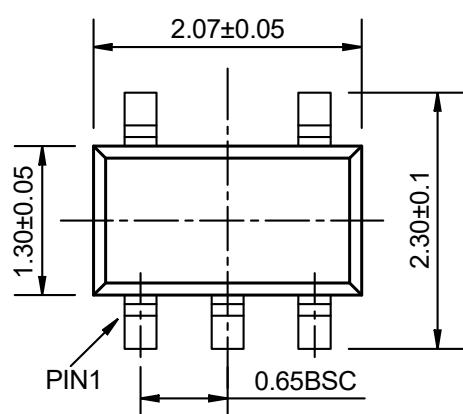
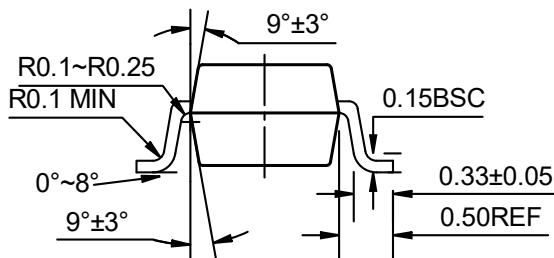
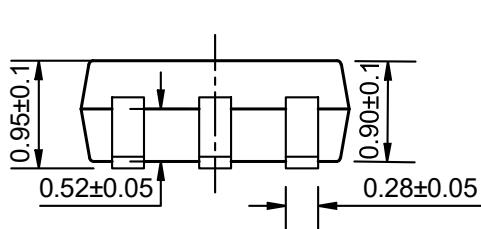


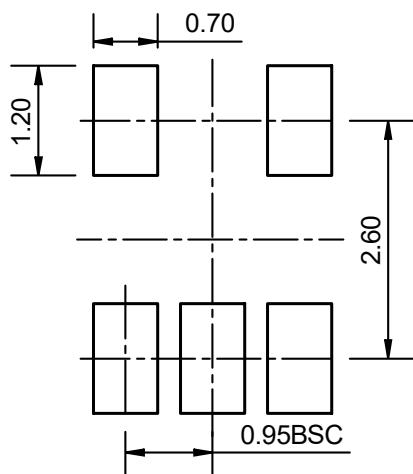
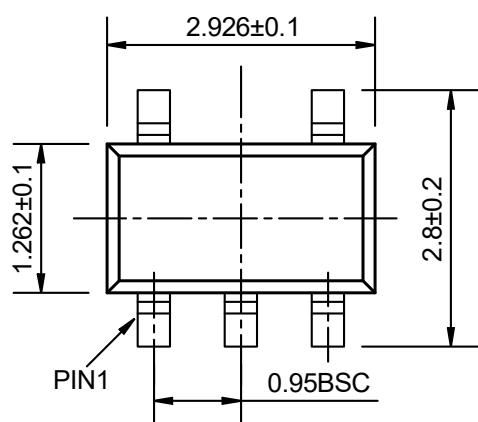
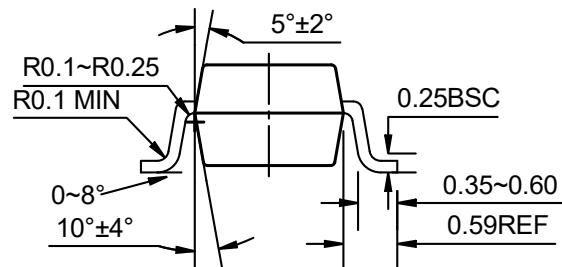
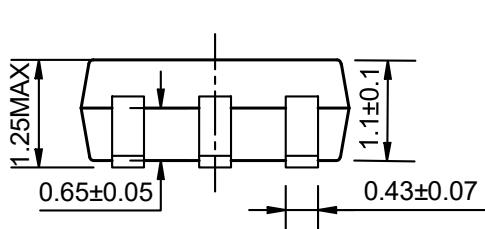
Figure 4. Test Circuit

Package Dimension

SC70-5

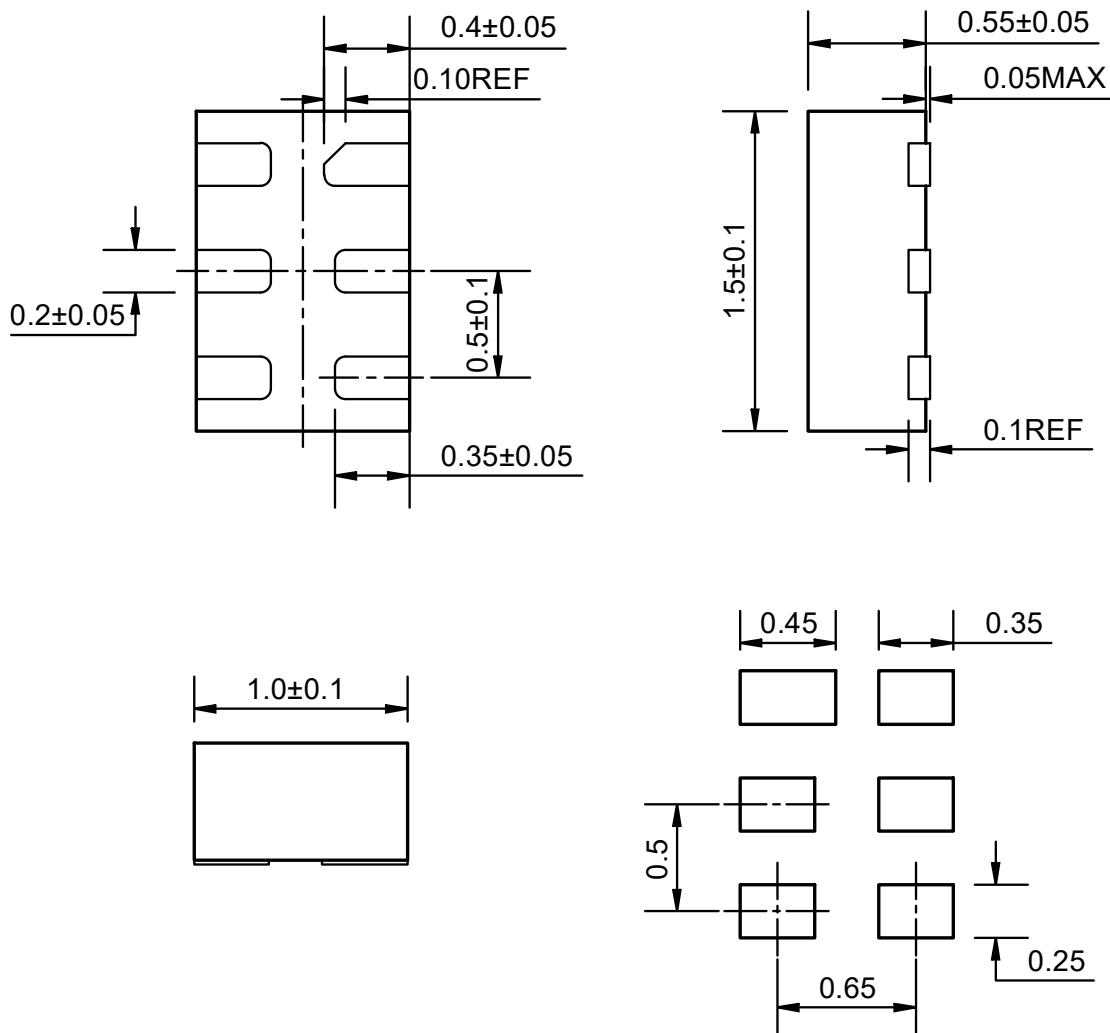
**Recommended Land Pattern**

SOT23-5



Recommended Land Pattern

DFN6



Recommended Land Pattern

Ordering information

Order code	Marking code	Package	Baseqty	Delivery mode
UMW SN74AUP1G126DCKR	HN5	SC70-5	3000	Tape and reel
UMW SN74AUP1G126DBVR	H26R	SOT23-5	3000	Tape and reel
UMW SN74AUP1G126DSFR	HN	DFN6	5000	Tape and reel

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[NLV7SZ97DFT2G](#) [NLVVHC1G14DFT2G](#) [NLX1G99DMUTWG](#) [NLVVHC1G00DFT2G](#) [NLV7SZ57DFT2G](#) [NLV74VHC04DTR2G](#)
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[NLVVHC1GT00DFT2G](#) [NLV74HC02ADTR2G](#) [NLX1G332CMUTCG](#) [NLVHCT132ADTR2G](#) [NL17SG86P5T5G](#) [NL17SZ05P5T5G](#)
[NLV74VHC00DTR2G](#) [NLVVHC1G02DFT1G](#) [NLV74HC86ADR2G](#)